



N- and P-Channel 2.5-V (G-S) MOSFET

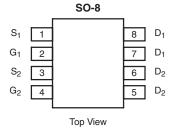
PRODUCT SUMMARY				
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
N-Channel	20	0.025 at V _{GS} = 4.5 V	7.1	
		0.035 at V _{GS} = 2.5 V	6.0	
P-Channel	- 20	0.033 at V _{GS} = - 4.5 V	- 6.2	
		0.050 at V _{GS} = - 2.5 V	- 5.0	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 2.5 Rated
- Compliant to RoHS directive 2002/95/EC

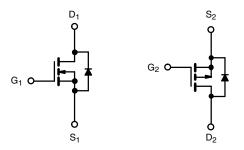


FREE



Ordering Information: Si4562DY-T1-E3 (Lead (Pb)-free)

Si4562DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V_{DS}	20 - 20		V	
Gate-Source Voltage		V_{GS}	±			
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _A = 25 °C	I _D	7.1	- 6.2		
Continuous Drain Current (1) = 150 °C)	T _A = 70 °C		5.7	- 4.9	A	
Pulsed Drain Current		I _{DM}	40 - 40		_ ^	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7 - 1.7			
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0		w	
Maximum Fower Dissipation	T _A = 70 °C	' D	1.3			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 1	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	N- or P-Channel	Unit		
Maximum Junction-to-Ambient ^a	R _{thJA}	62.5	°C/W		

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

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SPECIFICATIONS T _J = 25	°C, unle	ss otherwise noted						
Parameter	Symbol	Test Conditions		Min.	Тур.	Max.	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	0.6		1.6		
		$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	P-Ch	- 0.6		- 1.6	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	N-Ch P-Ch			± 100 ± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 20 V, V _{GS} = 0 V	N-Ch			1		
		V _{DS} = - 20 V, V _{GS} = 0 V	P-Ch			- 1		
	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			5	μΑ	
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	P-Ch			- 5		
On-State Drain Current ^b		$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N-Ch	20			А	
	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P-Ch	- 20				
		V _{GS} = 4.5 V, I _D = 7.1 A	N-Ch		0.019	0.025		
		V _{GS} = - 4.5 V, I _D = - 6.2 A	P-Ch		0.027	0.033		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 6.0 A	N-Ch		0.025	0.035	Ω	
		V _{GS} = - 2.5 V, I _D = - 5.0 A	P-Ch		0.040	0.050		
h	g _{fs}	$V_{DS} = 10 \text{ V}, I_D = 7.1 \text{ A}$	N-Ch		27		S	
Forward Transconductance ^b		V _{DS} = - 10 V, I _D = - 6.2 A	P-Ch		20			
5: 1 5 134 h	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	N-Ch			1.2	V	
Diode Forward Voltage ^b		I _S = - 1.7 A, V _{GS} = 0 V	P-Ch			- 1.2		
Dynamic ^b								
Total Gate Charge	O _n	Q _g N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 7.1 A	N-Ch		25	50		
Total date onlings	G g		P-Ch		22	35		
Gate-Source Charge	Q _{gs}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 6.2 A	N-Ch		6.5		nC	
			P-Ch		7			
Gate-Drain Charge			N-Ch P-Ch		3.5			
			N-Ch		40	60		
Turn-On Delay Time	t _{d(on)}	N-Channel $V_{DD} = 10 \text{ V}, R_L = 10 \Omega$	P-Ch		27	50		
Rise Time	t _r		N-Ch		40	60		
		$I_D \cong 1 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 6 \Omega$	P-Ch		32	50		
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch		90	150	ns	
	G(OII)	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$	P-Ch		95	150	-	
Fall Time	t _f	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω	N-Ch		40	60		
	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs	P-Ch		45	70		
Sorce-Drain Reverse Recovery Tme		$I_F = 1.7 \text{ A, dl/dt} = 100 \text{ A/µs}$ $I_F = -1.7 \text{ A, dl/dt} = 100 \text{ A/µs}$	N-Ch		40	80		
-		i _F = - 1.7 A, αί/αι = 100 A/μS	P-Ch		40	80		

Notes:

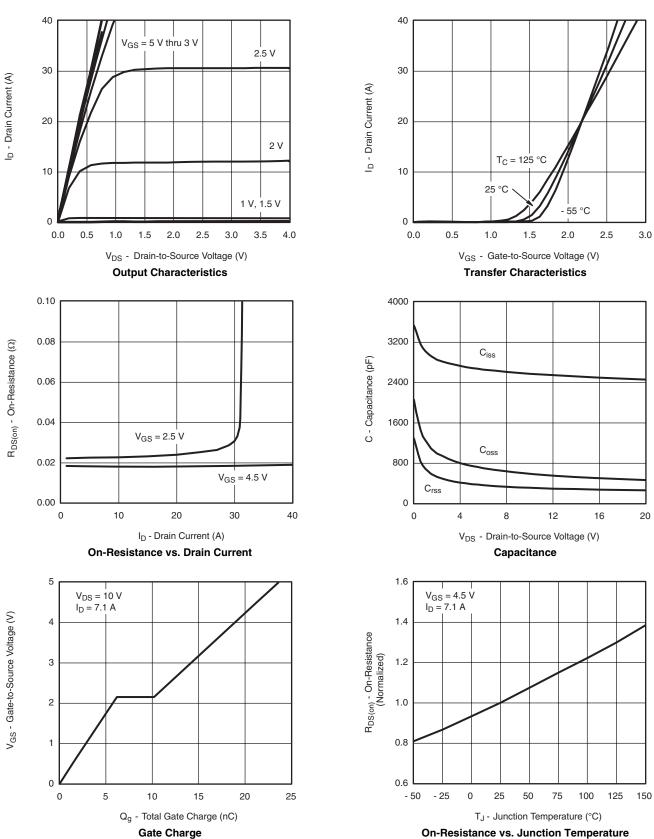
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. For design aid only; not subject to production testing. b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.





N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

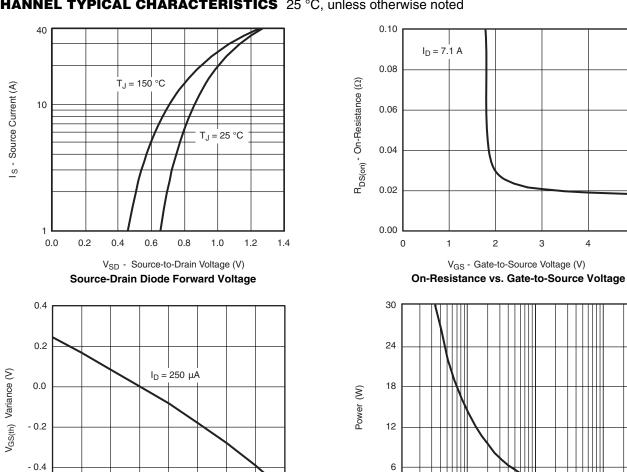


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N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T_J - Temperature (°C) **Threshold Voltage**

50

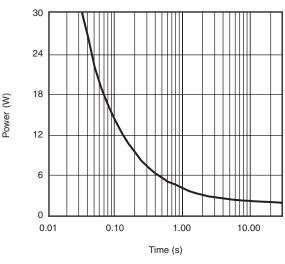
75

100

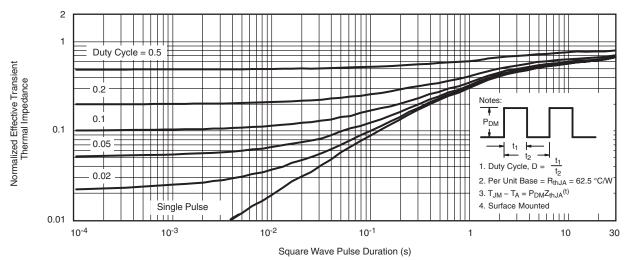
125

150

25



Single Pulse Power



- 0.6

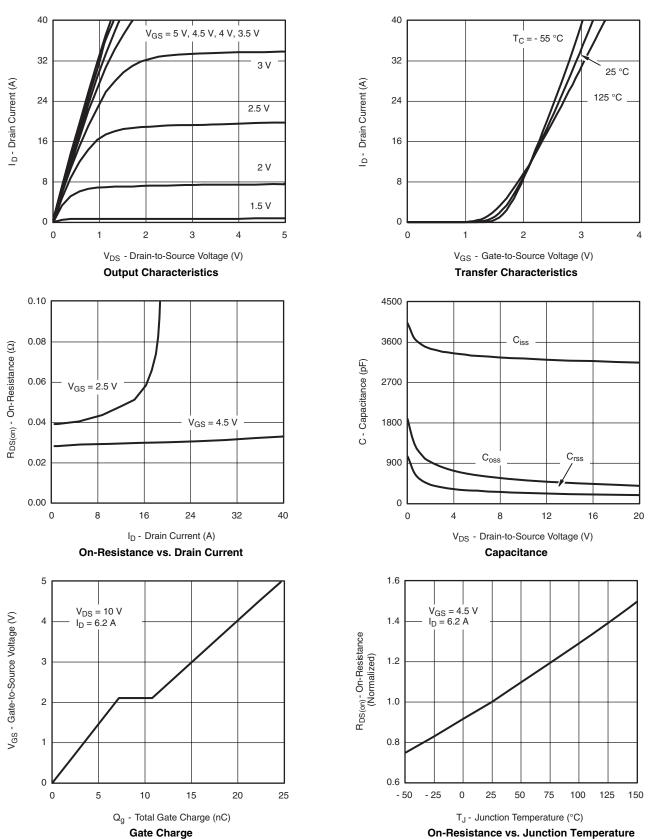
- 50

- 25





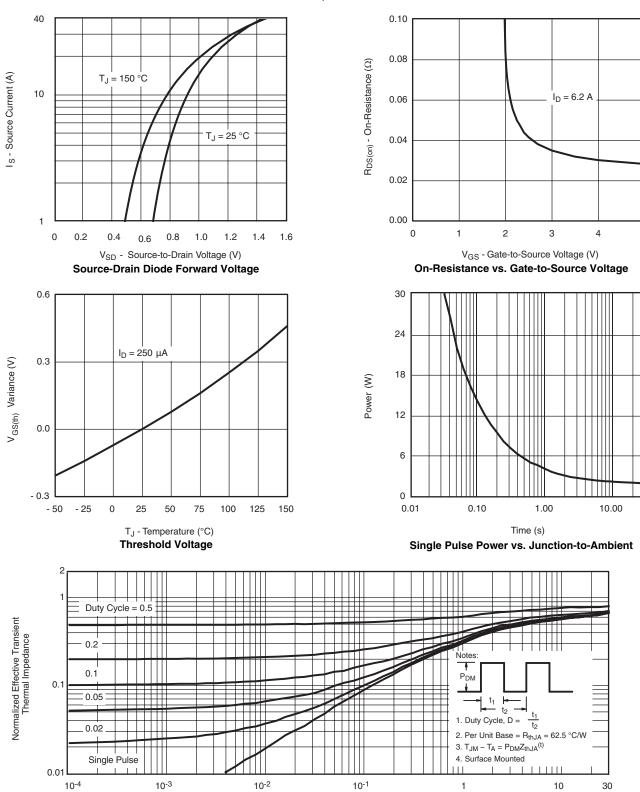
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)
Normalized Thermal Transient Impedance, Junction-to-Ambient

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